

SKM 400GB125D



SEMITRANS™ 3

Ultra Fast IGBT Modules

SKM 400GB125D

SKM 400GAL125D

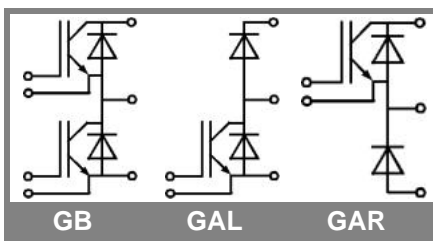
SKM 400GAR125D

Features

- N channel, homogeneous Si
- Low inductance case
- Short tail current with low temperature dependence
- High short circuit capability, self limiting to $6 \times I_{cnom}$
- Fast & soft inverse CAL diodes
- Isolated copper baseplate using DBC Direct Copper Bonding Technology
- Large clearance (13 mm) and creepage distances (20 mm)

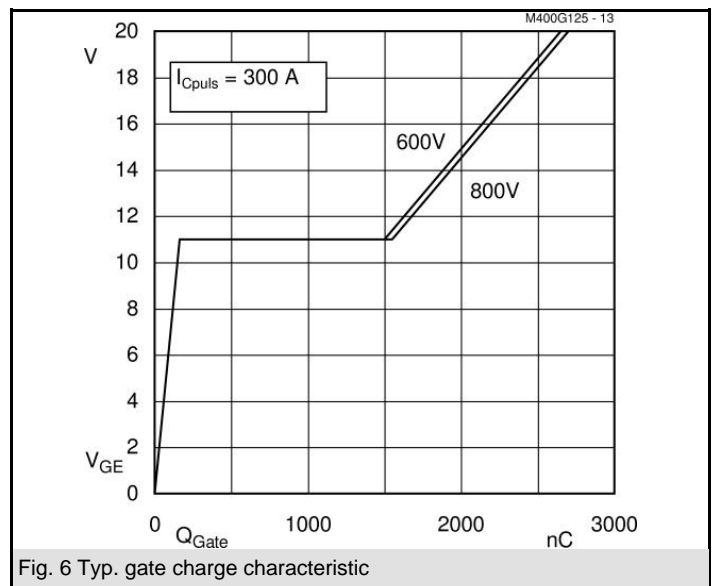
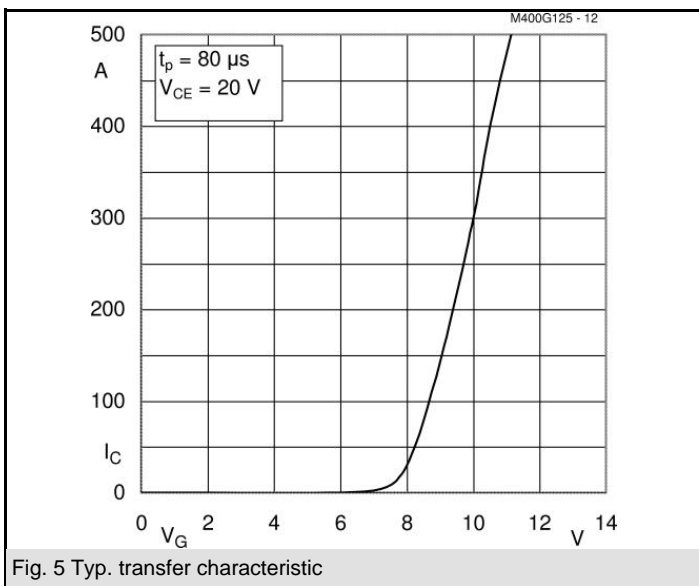
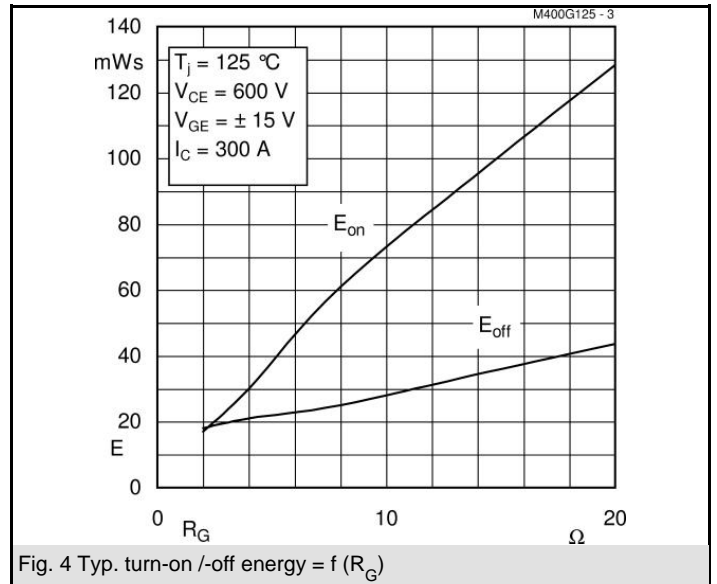
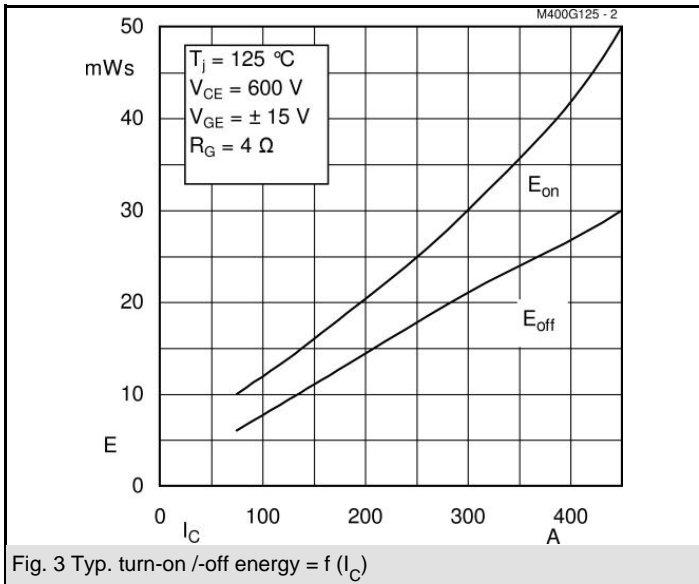
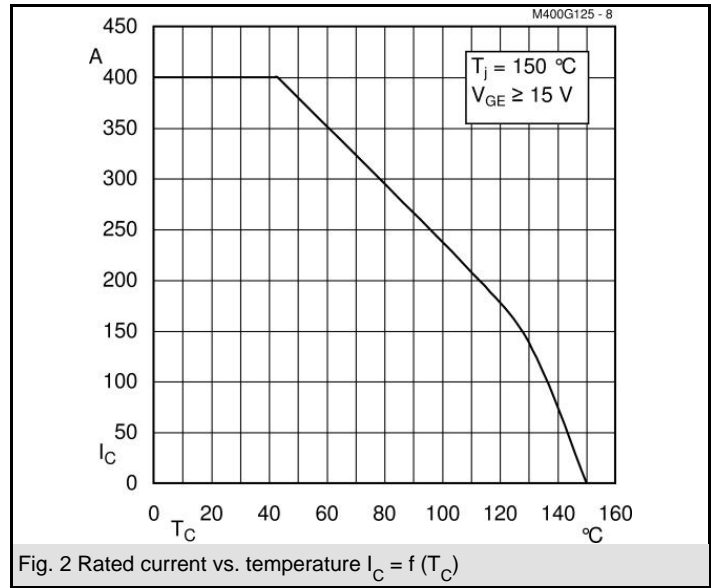
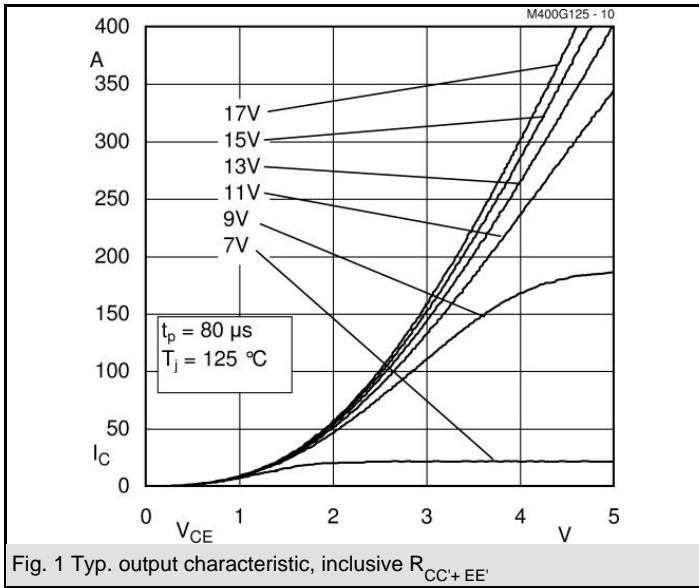
Typical Applications

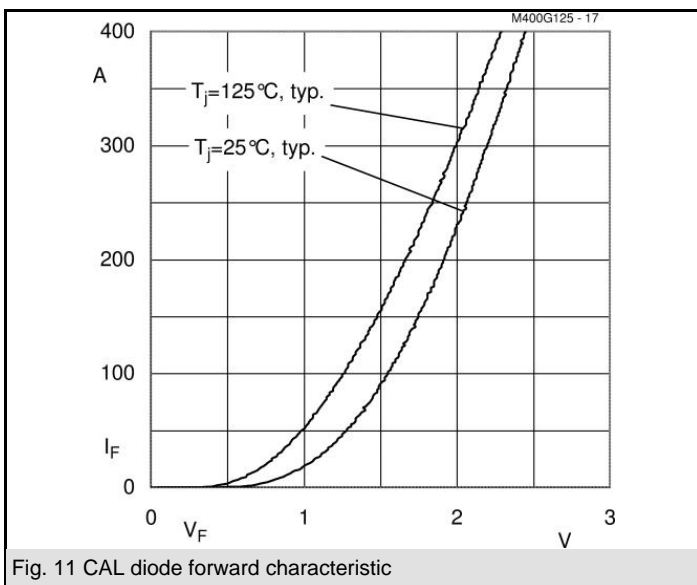
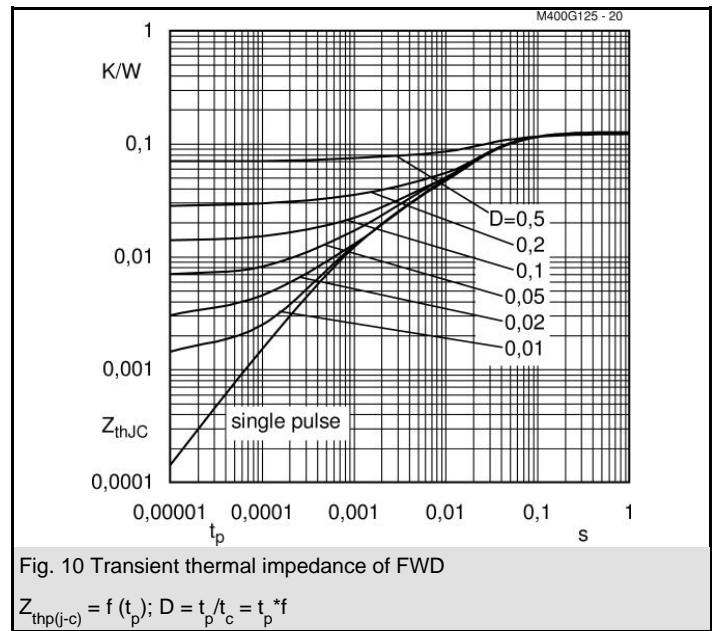
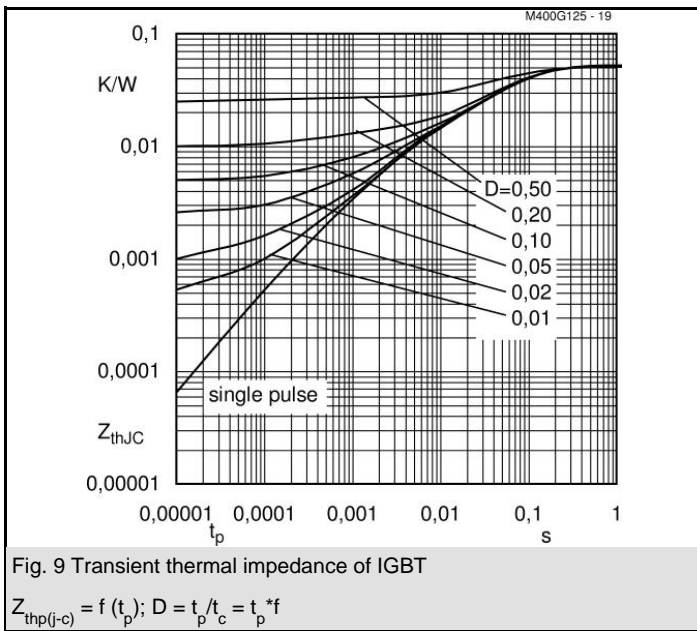
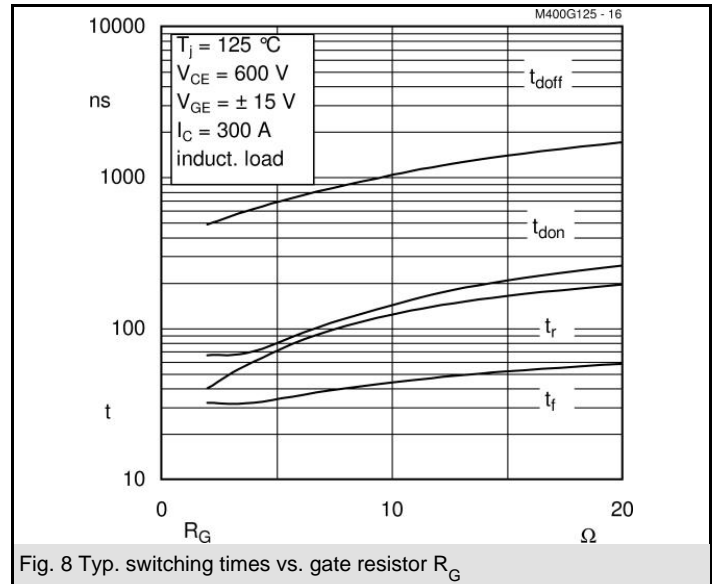
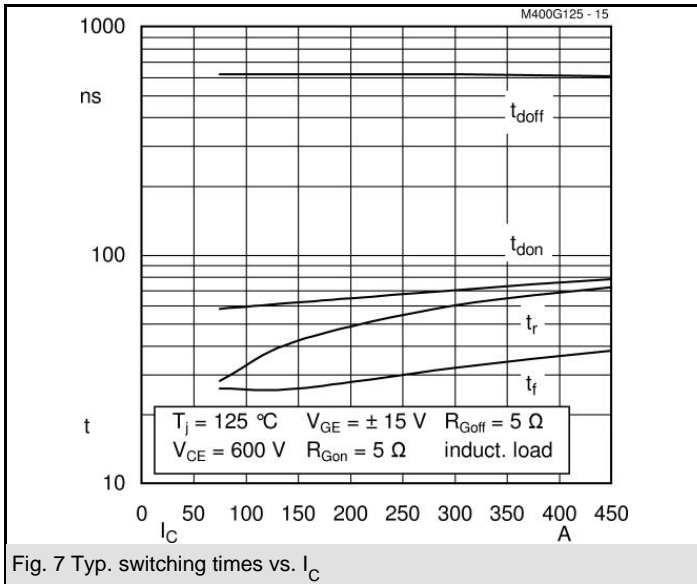
- Switched mode power supplies at $f_{sw} > 20\text{kHz}$
- Resonant inverters up to 100 kHz
- Inductive heating
- Electronic welders at $f_{sw} > 20\text{ kHz}$

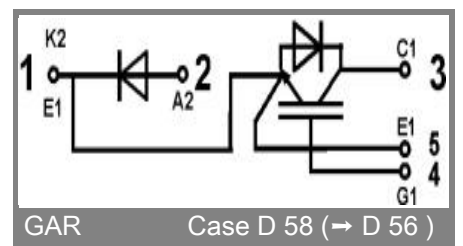
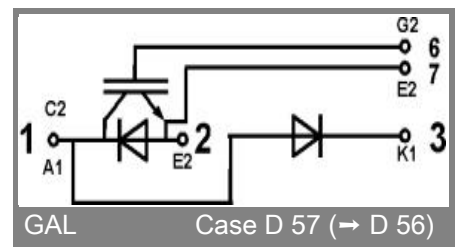
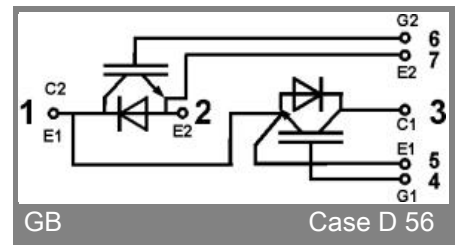
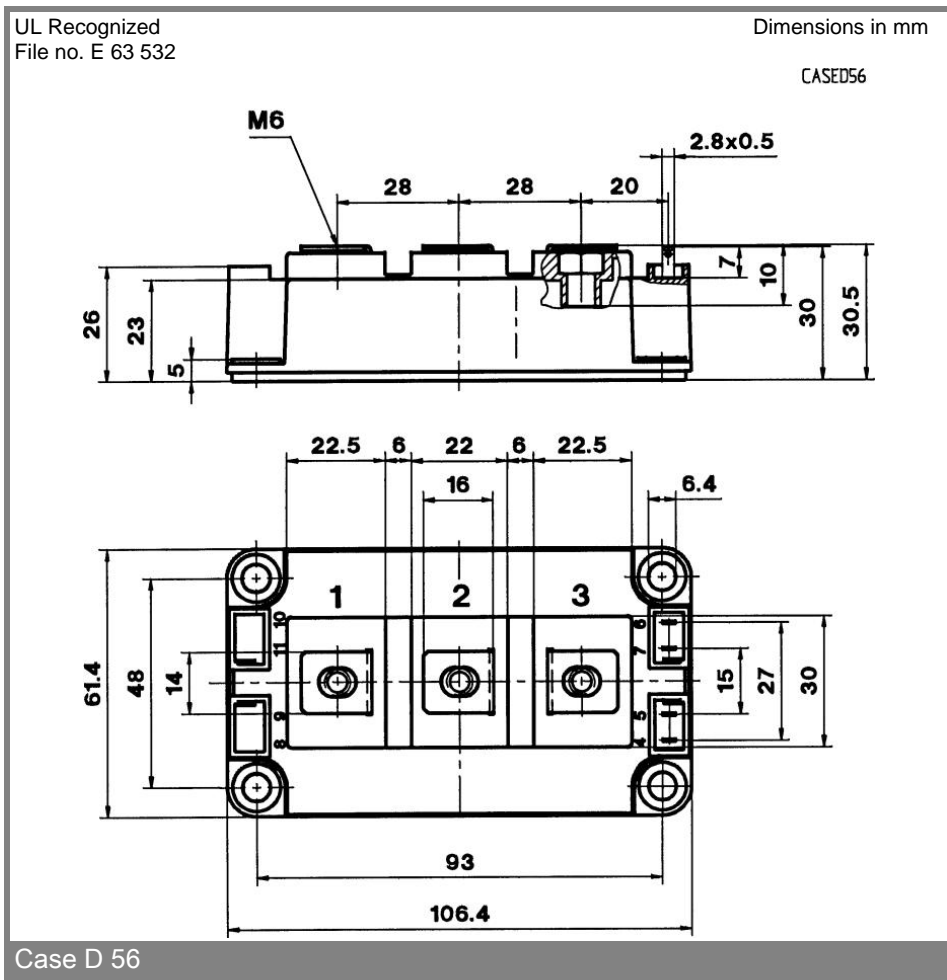


Absolute Maximum Ratings		$T_c = 25\text{ }^\circ\text{C}$, unless otherwise specified	
Symbol	Conditions	Values	Units
IGBT			
V_{CES}		1200	V
I_C	$T_c = 25\text{ (80) }^\circ\text{C}$	400 (300)	A
I_{CRM}	$T_c = 25\text{ (80) }^\circ\text{C}$, $t_p = 1\text{ ms}$	800 (600)	A
V_{GES}		± 20	V
T_{vj} (T_{stg})	$T_{OPERATION} \leq T_{stg}$	- 40 ... + 150 (125)	$^\circ\text{C}$
V_{isol}	AC, 1 min.	4000	V
Inverse diode			
I_F	$T_c = 25\text{ (80) }^\circ\text{C}$	390 (260)	A
I_{FRM}	$T_c = 25\text{ (80) }^\circ\text{C}$, $t_p = 1\text{ ms}$	800 (600)	A
I_{FSM}	$t_p = 10\text{ ms}$; sin.; $T_j = 150\text{ }^\circ\text{C}$	2900	A

Characteristics		$T_c = 25\text{ }^\circ\text{C}$, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
IGBT					
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 12\text{ mA}$	4,5	5,5	6,5	V
I_{CES}	$V_{GE} = 0$, $V_{CE} = V_{CES}$, $T_j = 25\text{ (125) }^\circ\text{C}$		0,15	0,45	mA
$V_{CE(TO)}$	$T_j = 25\text{ (125) }^\circ\text{C}$		1,4 (1,7)		V
r_{CE}	$V_{GE} = 15\text{ V}$, $T_j = 25\text{ (125) }^\circ\text{C}$				m Ω
$V_{CE(sat)}$	$I_C = 300\text{ A}$, $V_{GE} = 15\text{ V}$, chip level		3,3	3,85	V
C_{ies}	under following conditions		22	30	nF
C_{oes}	$V_{GE} = 0$, $V_{CE} = 25\text{ V}$, $f = 1\text{ MHz}$		3,3	4	nF
C_{res}			1,2	1,6	nF
L_{CE}				20	nH
$R_{CC'+EE'}$	res., terminal-chip $T_c = 25\text{ (125) }^\circ\text{C}$		0,35 (0,5)		m Ω
$t_{d(on)}$	$V_{CC} = 600\text{ V}$, $I_C = 300\text{ A}$		70		ns
t_r	$R_{Gon} = R_{Goff} = 2\text{ }^\circ\Omega$, $T_j = 125\text{ }^\circ\text{C}$		50		ns
$t_{d(off)}$	$V_{GE} = \pm 15\text{ V}$		500		ns
t_f			32		ns
$E_{on} (E_{off})$			17 (18)		mJ
Inverse diode					
$V_F = V_{EC}$	$I_F = 300\text{ A}$; $V_{GE} = 0\text{ V}$; $T_j = 25\text{ (125) }^\circ\text{C}$		2,2 (2)	2,5	V
$V_{(TO)}$	$T_j = 125\text{ () }^\circ\text{C}$			1,2	V
r_T	$T_j = 125\text{ () }^\circ\text{C}$		2,7	3,5	m Ω
I_{RRM}	$I_F = 300\text{ A}$; $T_j = 25\text{ (125) }^\circ\text{C}$		85 (140)		A
Q_{rr}	$di/dt = \text{A}/\mu\text{s}$		13 (40)		μC
E_{rr}	$V_{GE} = \text{V}$				mJ
Thermal characteristics					
$R_{th(j-c)}$	per IGBT			0,05	K/W
$R_{th(j-c)D}$	per Inverse Diode			0,125	K/W
$R_{th(c-s)}$	per module			0,038	K/W
Mechanical data					
M_s	to heatsink M6	3		5	Nm
M_t	to terminals M6				Nm
w				325	g







This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.